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Understanding <u>Embedded - FPGAs (Field Programmable Gate Array)</u>

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Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Active
Number of LABs/CLBs	9360
Number of Logic Elements/Cells	149760
Total RAM Bits	6635520
Number of I/O	475
Number of Gates	-
Voltage - Supply	1.16V ~ 1.24V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	896-BGA
Supplier Device Package	896-FBGA (31x31)
Purchase URL	https://www.e-xfl.com/product-detail/intel/ep4cgx150df31c8n

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Cyclone IV E industrial devices I7 are offered with extended operating temperature range.

Absolute Maximum Ratings

Absolute maximum ratings define the maximum operating conditions for Cyclone IV devices. The values are based on experiments conducted with the device and theoretical modeling of breakdown and damage mechanisms. The functional operation of the device is not implied at these conditions. Table 1–1 lists the absolute maximum ratings for Cyclone IV devices.



Conditions beyond those listed in Table 1–1 cause permanent damage to the device. Additionally, device operation at the absolute maximum ratings for extended periods of time have adverse effects on the device.

Table 1–1. Absolute Maximum Ratings for Cyclone IV Devices (1)

Symbol	Parameter	Min	Max	Unit
V _{CCINT}	Core voltage, PCI Express® (PCIe®) hard IP block, and transceiver physical coding sublayer (PCS) power supply	-0.5	1.8	V
V _{CCA}	Phase-locked loop (PLL) analog power supply	-0.5	3.75	V
V _{CCD_PLL}	PLL digital power supply	-0.5	1.8	V
V _{CCIO}	I/O banks power supply	-0.5	3.75	V
V _{CC_CLKIN}	Differential clock input pins power supply	-0.5	4.5	V
V _{CCH_GXB}	Transceiver output buffer power supply	-0.5	3.75	V
V _{CCA_GXB}	Transceiver physical medium attachment (PMA) and auxiliary power supply	-0.5	3.75	V
V _{CCL_GXB}	Transceiver PMA and auxiliary power supply	-0.5	1.8	V
VI	DC input voltage	-0.5	4.2	V
I _{OUT}	DC output current, per pin	-25	40	mA
T _{STG}	Storage temperature	-65	150	°C
T _J	Operating junction temperature	-40	125	°C

Note to Table 1-1:

Maximum Allowed Overshoot or Undershoot Voltage

During transitions, input signals may overshoot to the voltage shown in Table 1–2 and undershoot to -2.0 V for a magnitude of currents less than 100 mA and for periods shorter than 20 ns. Table 1-2 lists the maximum allowed input overshoot voltage and the duration of the overshoot voltage as a percentage over the lifetime of the device. The maximum allowed overshoot duration is specified as a percentage of high-time over the lifetime of the device.

⁽¹⁾ Supply voltage specifications apply to voltage readings taken at the device pins with respect to ground, not at the power supply.

Table 1–3. Recommended Operating Conditions for Cyclone IV E Devices (1), (2) (Part 2 of 2)

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{Diode}	Magnitude of DC current across PCI-clamp diode when enable	_	_	_	10	mA

Notes to Table 1-3:

- (1) Cyclone IV E 1.0 V core voltage devices only support C8L, C9L, and I8L speed grades. Cyclone IV E 1.2 V core voltage devices only support C6, C7, C8, I7, and A7 speed grades.
- (2) V_{CCIO} for all I/O banks must be powered up during device operation. All VCCA pins must be powered to 2.5 V (even when PLLs are not used) and must be powered up and powered down at the same time.
- (3) V_{CC} must rise monotonically.
- (4) V_{CCIO} powers all input buffers.
- (5) The POR time for Standard POR ranges between 50 and 200 ms. Each individual power supply must reach the recommended operating range within 50 ms.
- (6) The POR time for Fast POR ranges between 3 and 9 ms. Each individual power supply must reach the recommended operating range within 3 ms.

Table 1-4. Recommended Operating Conditions for Cyclone IV GX Devices (Part 1 of 2)

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{CCINT} (3)	Core voltage, PCIe hard IP block, and transceiver PCS power supply	_	1.16	1.2	1.24	V
V _{CCA} (1), (3)	PLL analog power supply	_	2.375	2.5	2.625	V
V _{CCD_PLL} (2)	PLL digital power supply	_	1.16	1.2	1.24	V
	I/O banks power supply for 3.3-V operation	_	3.135	3.3	3.465	V
	I/O banks power supply for 3.0-V operation	_	2.85	3	3.15	V
\/ (3). (4)	I/O banks power supply for 2.5-V operation	_	2.375	2.5	2.625	V
V _{CCIO} (3), (4)	I/O banks power supply for 1.8-V operation	_	1.71	1.8	1.89	V
	I/O banks power supply for 1.5-V operation	_	1.425	1.5	1.575	V
	I/O banks power supply for 1.2-V operation	_	1.14	1.2	1.26	V
	Differential clock input pins power supply for 3.3-V operation	_	3.135	3.3	3.465	V
	Differential clock input pins power supply for 3.0-V operation	_	2.85	3	3.15	V
V _{CC_CLKIN}	Differential clock input pins power supply for 2.5-V operation	_	2.375	2.5	2.625	V
(3), (5), (6)	Differential clock input pins power supply for 1.8-V operation	_	1.71	1.8	1.89	V
	Differential clock input pins power supply for 1.5-V operation	_	1.425	1.5	1.575	V
	Differential clock input pins power supply for 1.2-V operation	_	1.14	1.2	1.26	V
$V_{\text{CCH_GXB}}$	Transceiver output buffer power supply	_	2.375	2.5	2.625	V

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{CCA_GXB}	Transceiver PMA and auxiliary power supply	_	2.375	2.5	2.625	V
V _{CCL_GXB}	Transceiver PMA and auxiliary power supply	_	1.16	1.2	1.24	V
V _I	DC input voltage	_	-0.5		3.6	V
V ₀	DC output voltage	_	0	_	V _{CCIO}	V
т	Operating junction temperature	For commercial use	0		85	°C
T _J	Operating junction temperature	For industrial use	-40	_	100	°C
t _{RAMP}	Power supply ramp time	Standard power-on reset (POR) (7)	50 μs	_	50 ms	_
		Fast POR (8)	50 μs	_	3 ms	_
I _{Diode}	Magnitude of DC current across PCI-clamp diode when enabled	_	_	ı	10	mA

Notes to Table 1-4:

- (1) All VCCA pins must be powered to 2.5 V (even when PLLs are not used) and must be powered up and powered down at the same time.
- (2) You must connect V_{CCD PLL} to V_{CCINT} through a decoupling capacitor and ferrite bead.
- (3) Power supplies must rise monotonically.
- (4) V_{CCIO} for all I/O banks must be powered up during device operation. Configurations pins are powered up by V_{CCIO} of I/O Banks 3, 8, and 9 where I/O Banks 3 and 9 only support V_{CCIO} of 1.5, 1.8, 2.5, 3.0, and 3.3 V. For fast passive parallel (FPP) configuration mode, the V_{CCIO} level of I/O Bank 8 must be powered up to 1.5, 1.8, 2.5, 3.0, and 3.3 V.
- (5) You must set $V_{\text{CC_CLKIN}}$ to 2.5 V if you use CLKIN as a high-speed serial interface (HSSI) refclk or as a DIFFCLK input.
- (6) The CLKIN pins in I/O Banks 3B and 8B can support single-ended I/O standard when the pins are used to clock left PLLs in non-transceiver applications.
- (7) The POR time for Standard POR ranges between 50 and 200 ms. V_{CCINT}, V_{CCA}, and V_{CCIO} of I/O Banks 3, 8, and 9 must reach the recommended operating range within 50 ms.
- (8) The POR time for Fast POR ranges between 3 and 9 ms. V_{CCINT}, V_{CCA}, and V_{CCIO} of I/O Banks 3, 8, and 9 must reach the recommended operating range within 3 ms.

ESD Performance

This section lists the electrostatic discharge (ESD) voltages using the human body model (HBM) and charged device model (CDM) for Cyclone IV devices general purpose I/Os (GPIOs) and high-speed serial interface (HSSI) I/Os. Table 1–5 lists the ESD for Cyclone IV devices GPIOs and HSSI I/Os.

Table 1-5. ESD for Cyclone IV Devices GPIOs and HSSI I/Os

Symbol	Parameter	Passing Voltage	Unit
V	ESD voltage using the HBM (GPIOs) (1)	± 2000	V
VESDHBM	ESD using the HBM (HSSI I/Os) (2)	± 1000	V
V	ESD using the CDM (GPIOs)	± 500	V
VESDCDM	ESD using the CDM (HSSI I/Os) (2)	± 250	V

Notes to Table 1-5:

- (1) The passing voltage for EP4CGX15 and EP4CGX30 row I/Os is ±1000V.
- (2) This value is applicable only to Cyclone IV GX devices.

DC Characteristics

This section lists the I/O leakage current, pin capacitance, on-chip termination (OCT) tolerance, and bus hold specifications for Cyclone IV devices.

Supply Current

The device supply current requirement is the minimum current drawn from the power supply pins that can be used as a reference for power size planning. Use the Excel-based early power estimator (EPE) to get the supply current estimates for your design because these currents vary greatly with the resources used. Table 1–6 lists the I/O pin leakage current for Cyclone IV devices.

Table 1-6. I/O Pin Leakage Current for Cyclone IV Devices (1), (2)

Symbol	Parameter	Conditions	Device	Min	Тур	Max	Unit
I _I	Input pin leakage current	$V_I = 0 V \text{ to } V_{CCIOMAX}$		-10	_	10	μΑ
I _{OZ}	Tristated I/O pin leakage current	$V_0 = 0 \text{ V to } V_{\text{CCIOMAX}}$		-10	_	10	μΑ

Notes to Table 1-6:

- This value is specified for normal device operation. The value varies during device power-up. This applies for all V_{CCIO} settings (3.3, 3.0, 2.5, 1.8, 1.5, and 1.2 V).
- (2) The 10 μ A I/O leakage current limit is applicable when the internal clamping diode is off. A higher current can be observed when the diode is on.

Bus Hold

The bus hold retains the last valid logic state after the source driving it either enters the high impedance state or is removed. Each I/O pin has an option to enable bus hold in user mode. Bus hold is always disabled in configuration mode.

Table 1–7 lists bus hold specifications for Cyclone IV devices.

Table 1–7. Bus Hold Parameter for Cyclone IV Devices (Part 1 of 2) (1)

							V _{CCIO}	(V)						
Parameter	Condition	1.2		1.5		1.8		2.5		3.0		3.3		Unit
		Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
Bus hold low, sustaining current	V _{IN} > V _{IL} (maximum)	8	_	12	_	30	_	50	_	70	_	70	_	μА
Bus hold high, sustaining current	V _{IN} < V _{IL} (minimum)	-8	_	-12	_	-30	_	-50	_	-70	_	-70	_	μА
Bus hold low, overdrive current	0 V < V _{IN} < V _{CCIO}	_	125	_	175	_	200	_	300	_	500	_	500	μА
Bus hold high, overdrive current	0 V < V _{IN} < V _{CCIO}	_	-125	_	-175	_	-200	_	-300	_	-500	_	-500	μА

Table 1–7. Bus Hold Parameter for Cyclone IV Devices (Part 2 of 2) (1)

Parameter							V _{CCIO}	(V)						
	Condition	1	.2	1	1.5		.8	2	2.5 3.0 3		.3	Unit		
		Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
Bus hold trip point	_	0.3	0.9	0.375	1.125	0.68	1.07	0.7	1.7	0.8	2	0.8	2	V

Note to Table 1-7:

(1) Bus hold trip points are based on the calculated input voltages from the JEDEC standard.

OCT Specifications

Table 1–8 lists the variation of OCT without calibration across process, temperature, and voltage (PVT).

Table 1-8. Series OCT Without Calibration Specifications for Cyclone IV Devices

		Resistance		
Description	V _{CCIO} (V)	Commercial Maximum	Industrial, Extended industrial, and Automotive Maximum	Unit
	3.0	±30	±40	%
0 · 00 T ···	2.5	±30	±40	%
Series OCT without calibration	1.8	±40	±50	%
Canbration	1.5	±50	±50	%
	1.2	±50	±50	%

OCT calibration is automatically performed at device power-up for OCT-enabled I/Os.

Table 1–9 lists the OCT calibration accuracy at device power-up.

Table 1–9. Series OCT with Calibration at Device Power-Up Specifications for Cyclone IV Devices

		Calibration		
Description	V _{CCIO} (V)	Commercial Maximum Industrial, Ex industrial, Ex industrial, Automotive M		Unit
	3.0	±10	±10	%
Series OCT with	2.5	±10	±10	%
calibration at device	1.8	±10	±10	%
power-up	1.5	±10	±10	%
	1.2	±10	±10	%

Operating Conditions

Example 1–1 shows how to calculate the change of 50- Ω I/O impedance from 25°C at 3.0 V to 85°C at 3.15 V.

Example 1-1. Impedance Change

$$\Delta R_V = (3.15 - 3) \times 1000 \times -0.026 = -3.83$$

$$\Delta R_T = (85 - 25) \times 0.262 = 15.72$$

Because ΔR_V is negative,

$$MF_V = 1 / (3.83/100 + 1) = 0.963$$

Because ΔR_T is positive,

$$MF_T = 15.72/100 + 1 = 1.157$$

$$MF = 0.963 \times 1.157 = 1.114$$

$$R_{final} = 50 \times 1.114 = 55.71 \Omega$$

Pin Capacitance

Table 1–11 lists the pin capacitance for Cyclone IV devices.

Table 1–11. Pin Capacitance for Cyclone IV Devices (1)

Symbol	Parameter	Typical – Quad Flat Pack (QFP)	Typical – Quad Flat No Leads (QFN)	Typical – Ball-Grid Array (BGA)	Unit
C _{IOTB}	Input capacitance on top and bottom I/O pins	7	7	6	pF
C _{IOLR}	Input capacitance on right I/O pins	7	7	5	pF
C _{LVDSLR}	Input capacitance on right I/O pins with dedicated LVDS output	8	8	7	pF
C _{VREFLR} (2)	Input capacitance on right dual-purpose $\ensuremath{\mathtt{VREF}}$ pin when used as V_{REF} or user I/O pin	21	21	21	pF
C _{VREFTB} (2)	Input capacitance on top and bottom dual-purpose ${\tt VREF}$ pin when used as $V_{{\tt REF}}$ or user I/O pin	23 (3)	23	23	pF
C _{CLKTB}	Input capacitance on top and bottom dedicated clock input pins	7	7	6	pF
C _{CLKLR}	Input capacitance on right dedicated clock input pins	6	6	5	pF

Notes to Table 1-11:

- (1) The pin capacitance applies to FBGA, UBGA, and MBGA packages.
- (2) When you use the VREF pin as a regular input or output, you can expect a reduced performance of toggle rate and t_{CO} because of higher pin capacitance.
- (3) C_{VREFTB} for the EP4CE22 device is 30 pF.

Internal Weak Pull-Up and Weak Pull-Down Resistor

Table 1-12 lists the weak pull-up and pull-down resistor values for Cyclone IV devices.

Table 1–12. Internal Weak Pull-Up and Weak Pull-Down Resistor Values for Cyclone IV Devices (1)

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		$V_{CCIO} = 3.3 \text{ V} \pm 5\%$ (2), (3)	7	25	41	kΩ
	Value of the I/O pin pull-up resistor	$V_{CCIO} = 3.0 \text{ V} \pm 5\%$ (2), (3)	7	28	47	kΩ
D	before and during configuration, as	$V_{CCIO} = 2.5 \text{ V} \pm 5\%$ (2), (3)	8	35	61	kΩ
R_ _{PU}	well as user mode if you enable the	$V_{CCIO} = 1.8 \text{ V} \pm 5\%$ (2), (3)	10	57	108	kΩ
	programmable pull-up resistor option	$V_{CCIO} = 1.5 \text{ V} \pm 5\%$ (2), (3)	13	82	163	kΩ
		$V_{CCIO} = 1.2 \text{ V} \pm 5\%$ (2), (3)	19	143	351	kΩ
		$V_{CCIO} = 3.3 \text{ V} \pm 5\%$ (4)	6	19	30	kΩ
	Velocities I/O discoull decomposition	$V_{CCIO} = 3.0 \text{ V} \pm 5\%$ (4)	6	22	36	kΩ
R_PD	Value of the I/O pin pull-down resistor before and during configuration	$V_{CCIO} = 2.5 \text{ V} \pm 5\%$ (4)	6	25	43	kΩ
	201010 and daring bonnigaration	$V_{CCIO} = 1.8 \text{ V} \pm 5\%$ (4)	7	35	71	kΩ
		$V_{CCIO} = 1.5 \text{ V} \pm 5\%$ (4)	8	50	112	kΩ

Notes to Table 1-12:

- (1) All I/O pins have an option to enable weak pull-up except the configuration, test, and JTAG pins. The weak pull-down feature is only available for JTAG TCK.
- (2) Pin pull-up resistance values may be lower if an external source drives the pin higher than V_{CCIO}.
- (3) $R_{PU} = (V_{CC10} V_1)/I_{R_PU}$ Minimum condition: $-40^{\circ}C$; $V_{CC10} = V_{CC} + 5\%$, $V_1 = V_{CC} + 5\% 50$ mV; Typical condition: $25^{\circ}C$; $V_{CC10} = V_{CC}$, $V_1 = 0$ V; $V_2 = 0$ V; $V_3 = 0$ V; $V_4 = 0$ V and $V_5 = 0$ V and $V_6 = 0$ V and $V_7 = 0$ V and $V_8 = 0$ V and $V_$

Maximum condition: 100°C ; $V_{\text{CCIO}} = V_{\text{CC}} - 5\%$, $V_{\text{I}} = 0$ V; in which V_{I} refers to the input voltage at the I/O pin.

(4) $R_{PD} = V_I/I_{RPD}$

Minimum condition: -40°C; $V_{CCIO} = V_{CC} + 5\%$, $V_I = 50$ mV;

Typical condition: 25°C; $V_{CCIO} = V_{CC}$, $V_1 = V_{CC} - 5\%$; Maximum condition: 100°C; $V_{CCIO} = V_{CC} - 5\%$, $V_1 = V_{CC} - 5\%$; in which V_1 refers to the input voltage at the I/O pin.

Hot-Socketing

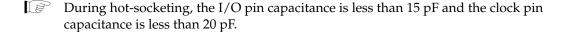
Table 1–13 lists the hot-socketing specifications for Cyclone IV devices.

Table 1–13. Hot-Socketing Specifications for Cyclone IV Devices

Symbol	Parameter	Maximum
I _{IOPIN(DC)}	DC current per I/O pin	300 μΑ
I _{IOPIN(AC)}	AC current per I/O pin	8 mA (1)
I _{XCVRTX(DC)}	DC current per transceiver TX pin	100 mA
I _{XCVRRX(DC)}	DC current per transceiver RX pin	50 mA

Note to Table 1-13:

(1) The I/O ramp rate is 10 ns or more. For ramp rates faster than 10 ns, $|IIOPIN| = C \frac{dv}{dt}$, in which C is the I/O pin capacitance and dv/dt is the slew rate.



For more information about receiver input and transmitter output waveforms, and for other differential I/O standards, refer to the I/O Features in Cyclone IV Devices chapter.

Table 1–18. Differential SSTL I/O Standard Specifications for Cyclone IV Devices (1)

I/O Standard	V	_{CC10} (V	')	V _{Swing}	_{J(DC)} (V)	V _{x(} ,	_{AC)} (V)		V _{Swi}	ng(AC) /)	V _{ox}	_(AC) (V)	
	Min	Тур	Max	Min	Max	Min	Тур	Max	Min	Max	Min	Тур	Max
SSTL-2 Class I, II	2.375	2.5	2.625	0.36	V _{CCIO}	V _{CCIO} /2 - 0.2	_	V _{CCIO} /2 + 0.2	0.7	V _{CCI}	V _{CCIO} /2 - 0.125	_	V _{CCIO} /2 + 0.125
SSTL-18 Class I, II	1.7	1.8	1.90	0.25	V _{CCIO}	V _{CCIO} /2 - 0.175	_	V _{CCIO} /2 + 0.175	0.5	V _{CCI}	V _{CCIO} /2 - 0.125	_	V _{CCIO} /2 + 0.125

Note to Table 1-18:

Table 1–19. Differential HSTL I/O Standard Specifications for Cyclone IV Devices (1)

	V	V _{CCIO} (V) V _D			_{DC)} (V)	V _x	_(AC) (V)		V	СМ(DC)	V)	V _{DII}	_{F(AC)} (V)
I/O Standard	Min	Тур	Max	Min	Max	Min	Тур	Max	Min	Тур	Max	Mi n	Max
HSTL-18 Class I, II	1.71	1.8	1.89	0.2	_	0.85		0.95	0.85	_	0.95	0.4	_
HSTL-15 Class I, II	1.425	1.5	1.575	0.2	_	0.71		0.79	0.71	_	0.79	0.4	_
HSTL-12 Class I, II	1.14	1.2	1.26	0.16	V _{CCIO}	0.48 x V _{CCIO}		0.52 x V _{CCIO}	0.48 x V _{CCIO}		0.52 x V _{CCIO}	0.3	0.48 x V _{CCIO}

Note to Table 1-19:

Table 1–20. Differential I/O Standard Specifications for Cyclone IV Devices (1) (Part 1 of 2)

I/O Standard		V _{CCIO} (V)		V _{ID}	(mV)		V _{ICM} (V) ⁽²⁾		Vo	_D (mV)	(3)	V _{0S} (V) ⁽³⁾		
i/O Stanuaru	Min	Тур	Max	Min	Max	Min	Condition	Max	Min	Тур	Max	Min	Тур	Max
LV/DEQL						0.05	$D_{MAX} \leq 500 \; Mbps$	1.80						
LVPECL (Row I/Os)	2.375	2.5	2.625	100	_	0.55	$\begin{array}{l} 500 \; \text{Mbps} \leq D_{\text{MAX}} \\ \leq 700 \; \text{Mbps} \end{array}$	1.80	_	_	_	_	_	_
						1.05	D _{MAX} > 700 Mbps	1.55						
IV/DEQL						0.05	$D_{MAX} \leq 500 \text{ Mbps}$	1.80						
LVPECL (Column I/Os) (6)	2.375	2.5	2.625	100	_	0.55	$\begin{array}{l} 500 \; \text{Mbps} \leq D_{\text{MAX}} \\ \leq 700 \; \text{Mbps} \end{array}$	1.80	_	_	_	_	_	_
1,00)						1.05	D _{MAX} > 700 Mbps	1.55						
						0.05	$D_{MAX} \leq 500 \; Mbps$	1.80						
LVDS (Row I/Os)	2.375	2.5	2.625	100	_	0.55	$\begin{array}{l} 500 \; \text{Mbps} \leq D_{\text{MAX}} \\ \leq \; 700 \; \text{Mbps} \end{array}$	1.80	247	_	600	1.125	1.25	1.375
						1.05	D _{MAX} > 700 Mbps	1.55						

⁽¹⁾ Differential SSTL requires a V_{REF} input.

⁽¹⁾ Differential HSTL requires a V_{REF} input.

Table 1–21. Transceiver Specification for Cyclone IV GX Devices (Part 4 of 4)

Symbol/	Conditions		C6			C7, I7			C8		Unit
Description	Collultions	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Unit
PLD-Transceiver Inte	rface										
Interface speed (F324 and smaller package)	_	25	_	125	25	_	125	25	_	125	MHz
Interface speed (F484 and larger package)	_	25	_	156.25	25	_	156.25	25	_	156.25	MHz
Digital reset pulse width	_	Minimum is 2 parallel clock cycles									

Notes to Table 1-21:

- (1) This specification is valid for transmitter output jitter specification with a maximum total jitter value of 112 ps, typically for 3.125 Gbps SRIO and XAUI protocols.
- (2) The minimum reconfig_clk frequency is 2.5 MHz if the transceiver channel is configured in **Transmitter Only** mode. The minimum reconfig_clk frequency is 37.5 MHz if the transceiver channel is configured in **Receiver Only** or **Receiver and Transmitter** mode.
- (3) The device cannot tolerate prolonged operation at this absolute maximum.
- (4) The rate matcher supports only up to ±300 parts per million (ppm).
- (5) Supported for the F169 and F324 device packages only.
- (6) Supported for the F484, F672, and F896 device packages only. Pending device characterization.
- (7) To support CDR ppm tolerance greater than ±300 ppm, implement ppm detector in user logic and configure CDR to Manual Lock Mode.
- (8) Asynchronous spread-spectrum clocking is not supported.
- (9) For the EP4CGX30 (F484 package only), EP4CGX50, and EP4CGX75 devices, the CDR ppl tolerance is ±200 ppm.
- (10) Time taken until pll locked goes high after pll powerdown deasserts.
- (11) Time that the CDR must be kept in lock-to-reference mode after rx analogreset deasserts and before rx locktodata is asserted in manual mode.
- (12) Time taken to recover valid data after the rx_locktodata signal is asserted in manual mode (Figure 1–2), or after rx_freqlocked signal goes high in automatic mode (Figure 1–3).
- (13) Time taken to recover valid data after the $rx_locktodata$ signal is asserted in manual mode.
- (14) Time taken to recover valid data after the $rx_freqlocked$ signal goes high in automatic mode.
- (15) To support data rates lower than the minimum specification through oversampling, use the CDR in LTR mode only.

Figure 1–2 shows the lock time parameters in manual mode.

LTD = lock-to-data. LTR = lock-to-reference.

Figure 1–2. Lock Time Parameters for Manual Mode

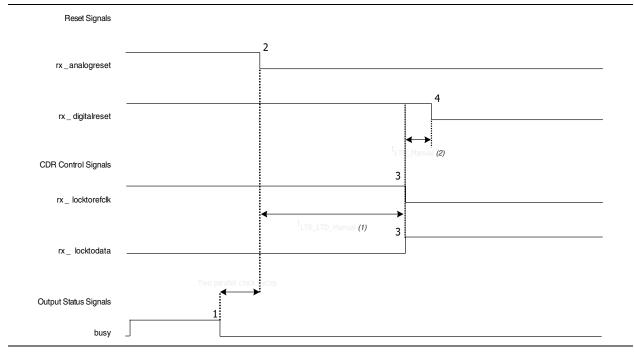


Figure 1–3 shows the lock time parameters in automatic mode.

Figure 1-3. Lock Time Parameters for Automatic Mode

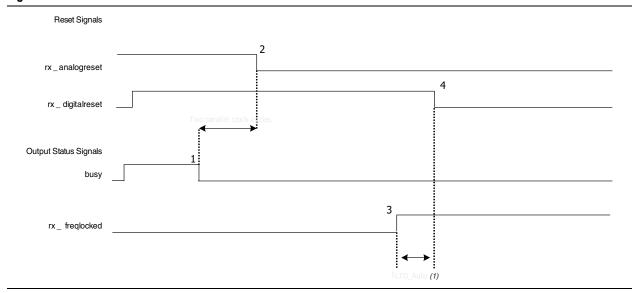


Figure 1–4 shows the differential receiver input waveform.

Figure 1-4. Receiver Input Waveform

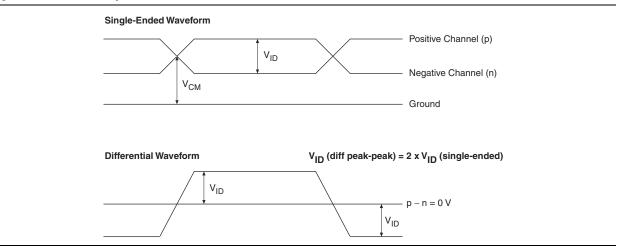


Figure 1–5 shows the transmitter output waveform.

Figure 1-5. Transmitter Output Waveform

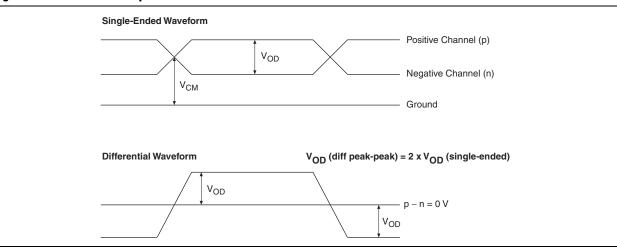


Table 1–22 lists the typical V_{OD} for Tx term that equals 100 Ω .

Table 1–22. Typical V_{OD} Setting, Tx Term = 100 Ω

Cumbal			V _{op} Sett	ing (mV)		
Symbol	1	2	3	4 (1)	5	6
V _{OD} differential peak to peak typical (mV)	400	600	800	900	1000	1200

Note to Table 1-22:

(1) This setting is required for compliance with the PCle protocol.

Table 1–24. Clock Tree Performance for Cyclone IV Devices (Part 2 of 2)

Dovice				Perfor	mance				Unit
Device	C6	C7	C8	C8L (1)	C9L (1)	17	I8L (1)	A7	Unit
EP4CE55	500	437.5	402	362	265	437.5	362	_	MHz
EP4CE75	500	437.5	402	362	265	437.5	362	_	MHz
EP4CE115	_	437.5	402	362	265	437.5	362	_	MHz
EP4CGX15	500	437.5	402	_	_	437.5	_	_	MHz
EP4CGX22	500	437.5	402	_	_	437.5	_	_	MHz
EP4CGX30	500	437.5	402	_	_	437.5	_	_	MHz
EP4CGX50	500	437.5	402	_	_	437.5	_	_	MHz
EP4CGX75	500	437.5	402	_	_	437.5	_	_	MHz
EP4CGX110	500	437.5	402	_	_	437.5	_	_	MHz
EP4CGX150	500	437.5	402	_	_	437.5	_	_	MHz

Note to Table 1-24:

PLL Specifications

Table 1–25 lists the PLL specifications for Cyclone IV devices when operating in the commercial junction temperature range (0°C to 85°C), the industrial junction temperature range (-40°C to 100°C), the extended industrial junction temperature range (-40°C to 125°C), and the automotive junction temperature range (-40°C to 125°C). For more information about the PLL block, refer to "Glossary" on page 1–37.

Table 1–25. PLL Specifications for Cyclone IV Devices (1), (2) (Part 1 of 2)

Symbol	Parameter	Min	Тур	Max	Unit
	Input clock frequency (-6, -7, -8 speed grades)	5	_	472.5	MHz
f _{IN} (3)	Input clock frequency (-8L speed grade)	5	_	362	MHz
	Input clock frequency (-9L speed grade)	5		265	MHz
f _{INPFD}	PFD input frequency	5		325	MHz
f _{VCO} (4)	PLL internal VCO operating range	600	_	1300	MHz
f _{INDUTY}	Input clock duty cycle	40	_	60	%
t _{INJITTER_CCJ} (5)	Input clock cycle-to-cycle jitter F _{REF} \geq 100 MHz	_	_	0.15	UI
	F _{REF} < 100 MHz	_	_	±750	ps
f _{OUT_EXT} (external clock output) (3)	PLL output frequency	_	_	472.5	MHz
	PLL output frequency (-6 speed grade)	_	_	472.5	MHz
	PLL output frequency (-7 speed grade)	_	_	450	MHz
f _{OUT} (to global clock)	PLL output frequency (-8 speed grade)	_	_	402.5	MHz
	PLL output frequency (-8L speed grade)	_	_	362	MHz
	PLL output frequency (-9L speed grade)	_	_	265	MHz
t _{outduty}	Duty cycle for external clock output (when set to 50%)	45	50	55	%
t _{LOCK}	Time required to lock from end of device configuration	_		1	ms

⁽¹⁾ Cyclone IV E 1.0 V core voltage devices only support C8L, C9L, and I8L speed grades.

Table 1–29 lists the active configuration mode specifications for Cyclone IV devices.

Table 1–29. Active Configuration Mode Specifications for Cyclone IV Devices

Programming Mode	DCLK Range	Typical DCLK	Unit
Active Parallel (AP) (1)	20 to 40	33	MHz
Active Serial (AS)	20 to 40	33	MHz

Note to Table 1-29:

(1) AP configuration mode is only supported for Cyclone IV E devices.

Table 1–30 lists the JTAG timing parameters and values for Cyclone IV devices.

Table 1–30. JTAG Timing Parameters for Cyclone IV Devices (1)

Symbol	Parameter	Min	Max	Unit
t _{JCP}	TCK clock period	40	_	ns
t _{JCH}	TCK clock high time	19	_	ns
t _{JCL}	TCK clock low time	19	_	ns
t _{JPSU_TDI}	JTAG port setup time for TDI	1	_	ns
t _{JPSU_TMS}	JTAG port setup time for TMS	3	_	ns
t_{JPH}	JTAG port hold time	10	_	ns
t _{JPCO}	JTAG port clock to output (2), (3)	_	15	ns
t _{JPZX}	JTAG port high impedance to valid output (2), (3)	_	15	ns
t _{JPXZ}	JTAG port valid output to high impedance (2), (3)	_	15	ns
t _{JSSU}	Capture register setup time	5	_	ns
t _{JSH}	Capture register hold time	10	_	ns
t _{JSCO}	Update register clock to output	_	25	ns
t _{JSZX}	Update register high impedance to valid output	_	25	ns
t _{JSXZ}	Update register valid output to high impedance		25	ns

Notes to Table 1-30:

- (1) For more information about JTAG waveforms, refer to "JTAG Waveform" in "Glossary" on page 1-37.
- (2) The specification is shown for 3.3-, 3.0-, and 2.5-V LVTTL/LVCMOS operation of JTAG pins. For 1.8-V LVTTL/LVCMOS and 1.5-V LVCMOS, the output time specification is 16 ns.
- (3) For EP4CGX22, EP4CGX30 (F324 and smaller package), EP4CGX110, and EP4CGX150 devices, the output time specification for 3.3-, 3.0-, and 2.5-V LVTTL/LVCMOS operation of JTAG pins is 16 ns. For 1.8-V LVTTL/LVCMOS and 1.5-V LVCMOS, the output time specification is 18 ns.

Periphery Performance

This section describes periphery performance, including high-speed I/O and external memory interface.

I/O performance supports several system interfaces, such as the high-speed I/O interface, external memory interface, and the PCI/PCI-X bus interface. I/Os using the SSTL-18 Class I termination standard can achieve up to the stated DDR2 SDRAM interfacing speeds. I/Os using general-purpose I/O standards such as 3.3-, 3.0-, 2.5-, 1.8-, or 1.5-LVTTL/LVCMOS are capable of a typical 200 MHz interfacing frequency with a 10 pF load.

For more information about the supported maximum clock rate, device and pin planning, IP implementation, and device termination, refer to Section III: System Performance Specifications of the External Memory Interfaces Handbook.



Actual achievable frequency depends on design- and system-specific factors. Perform HSPICE/IBIS simulations based on your specific design and system setup to determine the maximum achievable frequency in your system.

High-Speed I/O Specifications

Table 1–31 through Table 1–36 list the high-speed I/O timing for Cyclone IV devices. For definitions of high-speed timing specifications, refer to "Glossary" on page 1–37.

Table 1–31. RSDS Transmitter Timing Specifications for Cyclone IV Devices (1), (2), (4) (Part 1 of 2)

			C6			C7, I	7		C8, A	7		C8L, I	BL		C9L		
Symbol	Modes	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Unit
	×10	5	_	180	5	_	155.5	5	_	155.5	5		155.5	5	_	132.5	MHz
	×8	5		180	5		155.5	5	_	155.5	5		155.5	5	_	132.5	MHz
f _{HSCLK} (input clock	×7	5		180	5	_	155.5	5	_	155.5	5		155.5	5	_	132.5	MHz
frequency)	×4	5	_	180	5	_	155.5	5	_	155.5	5	_	155.5	5	_	132.5	MHz
1 37	×2	5	_	180	5		155.5	5	_	155.5	5		155.5	5	_	132.5	MHz
	×1	5		360	5	_	311	5	_	311	5		311	5	_	265	MHz
	×10	100	_	360	100		311	100	_	311	100		311	100	_	265	Mbps
	×8	80	_	360	80		311	80	_	311	80		311	80	_	265	Mbps
Device operation in	×7	70	_	360	70	_	311	70		311	70	_	311	70	_	265	Mbps
Mbps	×4	40	_	360	40		311	40	_	311	40		311	40	_	265	Mbps
'	×2	20	_	360	20		311	20	_	311	20		311	20	_	265	Mbps
	×1	10	_	360	10	_	311	10		311	10	_	311	10	_	265	Mbps
t _{DUTY}	_	45	_	55	45		55	45	_	55	45		55	45	_	55	%
Transmitter channel-to- channel skew (TCCS)	_	_	_	200	_	_	200	_	_	200	_	_	200	_	_	200	ps
Output jitter (peak to peak)	_	_	_	500	_	_	500	_	_	550	_	_	600	_	_	700	ps
t _{RISE}	$20 - 80\%$, $C_{LOAD} = 5 pF$	_	500	_	_	500	_	_	500	_	_	500	—	_	500	_	ps
t _{FALL}	20 – 80%, C _{LOAD} = 5 pF	_	500	_	_	500	1		500	_	_	500	ı	_	500		ps

Table 1–34. True LVDS Transmitter Timing Specifications for Cyclone IV Devices (1), (3	ue LVDS Transmitter Timing Specifications	for Cyclone IV Devices (1), (3)
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Cumbal	Madaa	C	6	C7	, I7	C8,	, A7	C8L	, I8L	C	9L	llmit
Symbol	Modes	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Unit
	×10	5	420	5	370	5	320	5	320	5	250	MHz
	×8	5	420	5	370	5	320	5	320	5	250	MHz
f _{HSCLK} (input	×7	5	420	5	370	5	320	5	320	5	250	MHz
clock frequency)	×4	5	420	5	370	5	320	5	320	5	250	MHz
, ,,,	×2	5	420	5	370	5	320	5	320	5	250	MHz
	×1	5	420	5	402.5	5	402.5	5	362	5	265	MHz
	×10	100	840	100	740	100	640	100	640	100	500	Mbps
	×8	80	840	80	740	80	640	80	640	80	500	Mbps
HSIODR	×7	70	840	70	740	70	640	70	640	70	500	Mbps
nolubh	×4	40	840	40	740	40	640	40	640	40	500	Mbps
	×2	20	840	20	740	20	640	20	640	20	500	Mbps
	×1	10	420	10	402.5	10	402.5	10	362	10	265	Mbps
t _{DUTY}	_	45	55	45	55	45	55	45	55	45	55	%
TCCS	_	_	200	_	200	_	200	_	200	_	200	ps
Output jitter (peak to peak)	_	_	500	_	500	_	550	_	600	_	700	ps
t _{LOCK} (2)	_	_	1	_	1	_	1	_	1	_	1	ms

Notes to Table 1-34:

- (1) Cyclone IV E—true LVDS transmitter is only supported at the output pin of Row I/O Banks 1, 2, 5, and 6. Cyclone IV GX—true LVDS transmitter is only supported at the output pin of Row I/O Banks 5 and 6.
- (2) t_{LOCK} is the time required for the PLL to lock from the end-of-device configuration.
- (3) Cyclone IV E 1.0 V core voltage devices only support C8L, C9L, and I8L speed grades. Cyclone IV E 1.2 V core voltage devices only support C6, C7, C8, I7, and A7 speed grades. Cyclone IV GX devices only support C6, C7, C8, and I7 speed grades.

Table 1–35. Emulated LVDS Transmitter Timing Specifications for Cyclone IV Devices (1), (3) (Part 1 of 2)

Combal	Madaa	C	6	C7,	, I7	C8,	A7	C8L,	, I8L	C	9L	IIi4
Symbol	Modes	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Unit
	×10	5	320	5	320	5	275	5	275	5	250	MHz
	×8	5	320	5	320	5	275	5	275	5	250	MHz
f _{HSCLK} (input clock	×7	5	320	5	320	5	275	5	275	5	250	MHz
frequency)	×4	5	320	5	320	5	275	5	275	5	250	MHz
, ,,	×2	5	320	5	320	5	275	5	275	5	250	MHz
	×1	5	402.5	5	402.5	5	402.5	5	362	5	265	MHz
	×10	100	640	100	640	100	550	100	550	100	500	Mbps
	×8	80	640	80	640	80	550	80	550	80	500	Mbps
HSIODR	×7	70	640	70	640	70	550	70	550	70	500	Mbps
HOIODI	×4	40	640	40	640	40	550	40	550	40	500	Mbps
	×2	20	640	20	640	20	550	20	550	20	500	Mbps
	×1	10	402.5	10	402.5	10	402.5	10	362	10	265	Mbps



For more information about the supported maximum clock rate, device and pin planning, IP implementation, and device termination, refer to *Section III: System Performance Specifications* of the *External Memory Interface Handbook*.

Table 1–37 lists the memory output clock jitter specifications for Cyclone IV devices.

Table 1–37. Memory Output Clock Jitter Specifications for Cyclone IV Devices (1), (2)

Parameter	Symbol	Min	Max	Unit
Clock period jitter	t _{JIT(per)}	-125	125	ps
Cycle-to-cycle period jitter	t _{JIT(cc)}	-200	200	ps
Duty cycle jitter	t _{JIT(duty)}	-150	150	ps

Notes to Table 1-37:

- Memory output clock jitter measurements are for 200 consecutive clock cycles, as specified in the JEDEC DDR2 standard.
- (2) The clock jitter specification applies to memory output clock pins generated using DDIO circuits clocked by a PLL output routed on a global clock (GCLK) network.

Duty Cycle Distortion Specifications

Table 1–38 lists the worst case duty cycle distortion for Cyclone IV devices.

Table 1–38. Duty Cycle Distortion on Cyclone IV Devices I/O Pins (1), (2), (3)

Symbol	C	6	C7	, 1 7	C8, I8	BL, A7	C	9L	Unit
Symbol	Min	Max	Min	Max	Min	Max	Min	Max	Ullit
Output Duty Cycle	45	55	45	55	45	55	45	55	%

Notes to Table 1-38:

- (1) The duty cycle distortion specification applies to clock outputs from the PLLs, global clock tree, and IOE driving the dedicated and general purpose I/O pins.
- (2) Cyclone IV devices meet the specified duty cycle distortion at the maximum output toggle rate for each combination of I/O standard and current strength.
- (3) Cyclone IV E 1.0 V core voltage devices only support C8L, C9L, and I8L speed grades. Cyclone IV E 1.2 V core voltage devices only support C6, C7, C8, I7, and A7 speed grades. Cyclone IV GX devices only support C6, C7, C8, and I7 speed grades.

OCT Calibration Timing Specification

Table 1–39 lists the duration of calibration for series OCT with calibration at device power-up for Cyclone IV devices.

Table 1–39. Timing Specification for Series OCT with Calibration at Device Power-Up for Cyclone IV Devices $^{(1)}$

Symbol	Description	Maximum	Units
t _{OCTCAL}	Duration of series OCT with calibration at device power-up	20	μs

Note to Table 1-39:

(1) OCT calibration takes place after device configuration and before entering user mode.

Table 1–42 and Table 1–43 list the IOE programmable delay for Cyclone IV E 1.2 V core voltage devices.

Table 1-42. IOE Programmable Delay on Column Pins for Cyclone IV E 1.2 V Core Voltage Devices (1), (2)

		Number					Max (Offset				
Parameter	Paths Affected	of	Min Offset	Fa	ast Corn	er			Unit			
		Setting		C6	17	A7	C6	C 7	C8	17	A7	
Input delay from pin to internal cells	Pad to I/O dataout to core	7	0	1.314	1.211	1.211	2.177	2.340	2.433	2.388	2.508	ns
Input delay from pin to input register	Pad to I/O input register	8	0	1.307	1.203	1.203	2.19	2.387	2.540	2.430	2.545	ns
Delay from output register to output pin	I/O output register to pad	2	0	0.437	0.402	0.402	0.747	0.820	0.880	0.834	0.873	ns
Input delay from dual-purpose clock pin to fan-out destinations	Pad to global clock network	12	0	0.693	0.665	0.665	1.200	1.379	1.532	1.393	1.441	ns

Notes to Table 1-42:

- (1) The incremental values for the settings are generally linear. For the exact values for each setting, use the latest version of the Quartus II software.
- (2) The minimum and maximum offset timing numbers are in reference to setting **0** as available in the Quartus II software.

Table 1–43. IOE Programmable Delay on Row Pins for Cyclone IV E 1.2 V Core Voltage Devices (1), (2)

		Number					Max (Offset				
Parameter	Paths Affected	of	Min Offset	Fa	ast Corn	er		SI	ow Corn	er		Unit
		Setting		C6	17	A7	C6	C 7	C8	17	A7	
Input delay from pin to internal cells	Pad to I/O dataout to core	7	0	1.314	1.209	1.209	2.201	2.386	2.510	2.429	2.548	ns
Input delay from pin to input register	Pad to I/O input register	8	0	1.312	1.207	1.207	2.202	2.402	2.558	2.447	2.557	ns
Delay from output register to output pin	I/O output register to pad	2	0	0.458	0.419	0.419	0.783	0.861	0.924	0.875	0.915	ns
Input delay from dual-purpose clock pin to fan-out destinations	Pad to global clock network	12	0	0.686	0.657	0.657	1.185	1.360	1.506	1.376	1.422	ns

Notes to Table 1-43:

- (1) The incremental values for the settings are generally linear. For the exact values for each setting, use the latest version of the Quartus II software.
- (2) The minimum and maximum offset timing numbers are in reference to setting 0 as available in the Quartus II software.

Table 1–44 and Table 1–45 list the IOE programmable delay for Cyclone IV GX devices.

Table 1–44. IOE Programmable Delay on Column Pins for Cyclone IV GX Devices (1), (2)

		Number				Max (Offset			
Parameter	Paths Affected	of	Min Offset	Fast (Corner		Slow (Corner		Unit
		Settings		C6	17	C6	C7	C8	17	
Input delay from pin to internal cells	Pad to I/O dataout to core	7	0	1.313	1.209	2.184	2.336	2.451	2.387	ns
Input delay from pin to input register	Pad to I/O input register	8	0	1.312	1.208	2.200	2.399	2.554	2.446	ns
Delay from output register to output pin	I/O output register to pad	2	0	0.438	0.404	0.751	0.825	0.886	0.839	ns
Input delay from dual-purpose clock pin to fan-out destinations	Pad to global clock network	12	0	0.713	0.682	1.228	1.41	1.566	1.424	ns

Notes to Table 1-44:

- (1) The incremental values for the settings are generally linear. For exact values of each setting, use the latest version of the Quartus II software.
- (2) The minimum and maximum offset timing numbers are in reference to setting 0 as available in the Quartus II software.

Table 1-45. IOE Programmable Delay on Row Pins for Cyclone IV GX Devices (1), (2)

		Number				Max (Offset			
Parameter	Paths Affected	of	Min Offset	Fast (Corner		Slow (Corner		Unit
		Settings		C6	17	C6	C 7	C8	17	
Input delay from pin to internal cells	Pad to I/O dataout to core	7	0	1.314	1.210	2.209	2.398	2.526	2.443	ns
Input delay from pin to input register	Pad to I/O input register	8	0	1.313	1.208	2.205	2.406	2.563	2.450	ns
Delay from output register to output pin	I/O output register to pad	2	0	0.461	0.421	0.789	0.869	0.933	0.884	ns
Input delay from dual-purpose clock pin to fan-out destinations	Pad to global clock network	12	0	0.712	0.682	1.225	1.407	1.562	1.421	ns

Notes to Table 1-45:

- (1) The incremental values for the settings are generally linear. For exact values of each setting, use the latest version of Quartus II software.
- (2) The minimum and maximum offset timing numbers are in reference to setting 0 as available in the Quartus II software

Table 1-46. Glossary (Part 4 of 5)

ter	Term	Definitions
	t _C	High-speed receiver and transmitter input and output clock period.
	Channel-to- channel-skew (TCCS)	High-speed I/O block: The timing difference between the fastest and slowest output edges, including t_{CO} variation and clock skew. The clock is included in the TCCS measurement.
	t _{cin}	Delay from the clock pad to the I/O input register.
	t _{co}	Delay from the clock pad to the I/O output.
	t _{cout}	Delay from the clock pad to the I/O output register.
	t _{DUTY}	High-speed I/O block: Duty cycle on high-speed transmitter output clock.
	t _{FALL}	Signal high-to-low transition time (80–20%).
	t _H	Input register hold time.
	Timing Unit Interval (TUI)	High-speed I/O block: The timing budget allowed for skew, propagation delays, and data sampling window. (TUI = $1/(Receiver\ Input\ Clock\ Frequency\ Multiplication\ Factor) = t_C/w)$.
	t _{INJITTER}	Period jitter on the PLL clock input.
	t _{OUTJITTER_DEDCLK}	Period jitter on the dedicated clock output driven by a PLL.
	t _{OUTJITTER_IO}	Period jitter on the general purpose I/O driven by a PLL.
	t _{pllcin}	Delay from the PLL inclk pad to the I/O input register.
	t _{pllcout}	Delay from the PLL inclk pad to the I/O output register.
	Transmitter Output Waveform	Transmitter output waveforms for the LVDS, mini-LVDS, PPDS and RSDS Differential I/O Standards: Single-Ended Waveform Positive Channel (p) = V _{OH} Negative Channel (n) = V _{OL} Ground Differential Waveform (Mathematical Function of Positive & Negative Channel)
	t _{RISE}	Signal low-to-high transition time (20–80%).
	t _{SU}	Input register setup time.
J	_	_